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**CLAIMS**

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[Claim(s)]

[Claim 1] The resin-seal surface mount type semiconductor device with which the rear-face section of the internal derivation lead to which the aforementioned internal wiring is connected is characterized by the external electrode and bird clapper at the time of mounting a direct semiconductor device in the resin-seal surface mount type semiconductor device which carries a semiconductor device, wires an internal derivation lead in the electrode on the front face of an element, and comes to carry out the resin seal of the wiring section and the aforementioned semiconductor device section.

[Claim 2] The resin-seal surface mount type semiconductor device according to claim 1 characterized by the rear face of a semiconductor device being exposed to the outside of a semiconductor device through resin material other than a direct or closure resin.

[Claim 3] The resin-seal surface mount type semiconductor device according to claim 1 characterized by forming more highly one step than the field of an external electrode the field through the rear-face section of a semiconductor device, or resin material other than a closure resin.

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[Translation done.]

# PATENT ABSTRACTS OF JAPAN

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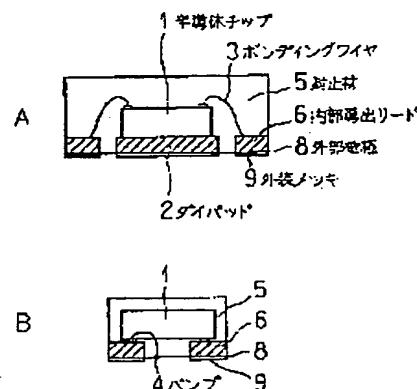
(21)Application number : 03-289882 (71)Applicant : SONY CORP  
 (22)Date of filing : 06.11.1991 (72)Inventor : FUKAZAWA HIROYUKI

## (54) RESIN-SEALED SURFACE-MOUNTING SEMICONDUCTOR DEVICE

### (57)Abstract:

**PURPOSE:** To reduce the size and thickness of the title semiconductor device while a mechanism which prevents the deformation of external electrodes or fluctuation of the electrodes at the machining time is secured by using the rear sections of inner leads connected to internal wiring as external electrodes at the time of directly mounting the semiconductor device.

**CONSTITUTION:** A semiconductor chip 1 is placed on the die pad 2 of a lead frame. After electrically connecting the chip 1 to inner leads 6, the rear of which become external electrodes 8, through bonding wires 3, the upper part is sealed with a resin. Similarly, the chip 1 is electrically connected to the leads through bumps 4. In other words, the rear of the electrically connected inner leads 6 are used as the electrical connecting sections 8 of the semiconductor device to the outside. Therefore, the size of the semiconductor device can be reduced to nearly the same size as that of the chip 1. In addition, the thickness of the semiconductor device can also be reduced.



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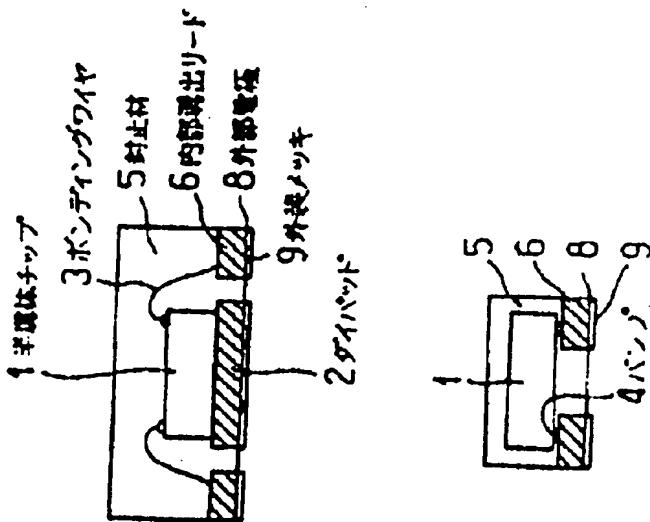
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Mould package flat-face mounting type semiconductor device  
exposes bottom surfaces of die pad and inner leads of bottom surface  
of mould package semiconductor device to be directly connected to  
circuit pattern of PCB NoAbstract

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